

MOTOROLA SEMICONDUCTOR TECHNICAL DATA

BUT35

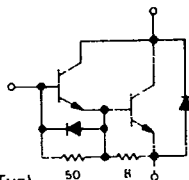
SWITCHMODE SERIES NPN SILICON POWER DARLINGTON TRANSISTORS WITH BASE-EMITTER SPEEDUP DIODE

The BUT35 Darlington transistor is designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switchmode applications such as:

- AC and DC Motor Controls
- Switching Regulators
- Inverters
- Solenoid and Relay Drivers
- Fast Turn-Off Times

550 nS Inductive Fall Time at 25°C (Typ)
2.5 μ S Inductive Storage Time at 25°C (Typ)

- Operating Temperature Range -65 to 200°C

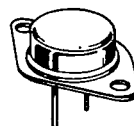


40 AMPERES NPN SILICON POWER DARLINGTON TRANSISTORS

1000 VOLTS
250 WATTS

Designer's Data for "Worst Case" Conditions

The Designer's Data Sheet permits the design of most circuits entirely from the information presented. Limit data - representing device characteristics boundaries - are given to facilitate "worst case" design.



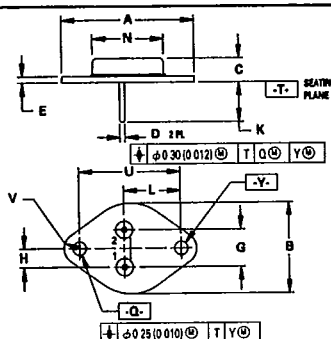
MAXIMUM RATINGS

Rating	Symbol	BUT35	Unit
Collector-Emitter Voltage	$V_{CE(sus)}$	700	Vdc
Collector-Emitter Voltage	V_{CEV}	1000	Vdc
Emitter-Base Voltage	V_{EB}	10	Vdc
Collector Current	I_C	40	Adc
Continuous	I_{CM}	50	Adc
Base Current	I_B	10	Adc
- Continuous	I_{BM}	20	Adc
Free Wheel Diode			
Forward current	I_F	40	Adc
Peak	I_{FM}	50	Adc
Total Power Dissipation	P_D	250	Watts
(at $T_C = 25^\circ\text{C}$)		140	
Derate above 25°C			W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	°C/W
Maximum Lead Temperature for Soldering Purpose	T_L	275	°C
1/8" from Case for 5 Seconds			

(1) Pulse Test Pulse Width = 5 ms, Duty Cycle $\leq$ 10%.



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION, INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	38.86 REF		1.530 REF	
B	25.15	26.67	0.990	1.050
C	6.35	8.25	0.250	0.325
D	1.45	1.60	0.057	0.063
E	1.53	1.77	0.060	0.070
G	10.92 BSC		0.430 BSC	
H	5.46 BSC		0.215 BSC	
K	11.18	12.19	0.440	0.480
L	16.89 BSC		0.665 BSC	
N	19.31	21.08	0.760	0.830
Q	3.84	4.19	0.151	0.165
U	30.15 BSC		1.187 BSC	
V	3.33	4.77	0.131	0.188

STYLE 1.
PIN 1. BASE
2. EMITTER
CASE. COLLECTOR

CASE 197A-02
TO-204AE
(TO-3)

ELECTRICAL CHARACTERISTICS (TC = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Table 1) (IC = 100 mA, IB = 0)	VCE(sus)	700	—	—	Vdc
Collector Cutoff Current (VCEV = Rated Value, VBE(off) = 1.5 Vdc) (VCEV = Rated Value, VBE(off) = 1.5 Vdc, TC = 100°C)	ICEV	—	—	0.2 4.0	mA _{dc}
Emitter Cutoff Current (VEB = 2.0 V, IC = 0)	IEBO	—	—	350	mA _{dc}

SECOND BREAKDOWN

Second Breakdown Collector Current with base forward biased	IS/b		See Figure 16	
Clamped Inductive SOA with Base Reverse Biased	RBSOA		See Figure 17	

ON CHARACTERISTICS (1)

DC Current Gain (IC = 12 A, VCE = 5 V) (IC = 24 A, VCE = 5 V)	hFE	30 15	— —	— —	
Collector-Emitter Saturation Voltage (IC = 12 A, IB = 0.6 A) (IC = 24 A, IB = 2.4 A) (IC = 32 A, IB = 3.2 A) (IC = 40 A, IB = 8 A)	VCE(sat)	— — — —	— — — —	2.0 3.0 3.5 5.0	Vdc
Base-Emitter Saturation Voltage (IC = 12 A, IB = 0.6 A) (IC = 24 A, IB = 2.4 A) (IC = 32 A, IB = 3.2 A)	VBE(sat)	— — —	— — —	2.5 2.9 3.3	Vdc
Diode Forward Voltage (IF = 32 A)	VF	—	—	4.0	Vdc

SWITCHING CHARACTERISTICS

Inductive Load, Clamped (Table 1)

Storage Time	TC 25°C	See Table 1 IC = 24 A	ts	—	—	4.0	μs
Fall Time			tf	—	—	1.2	μs
Storage Time	TC 100°C	IB1 = 2.4 A VBE(off) = 5 V	ts	—	2.8	—	μs
Fall Time			tf	—	0.65	—	μs

(1) Pulse Test PW 300 μs. Duty Cycle ≤ 2%

TYPICAL CHARACTERISTICS

FIGURE 1 — DC CURRENT GAIN

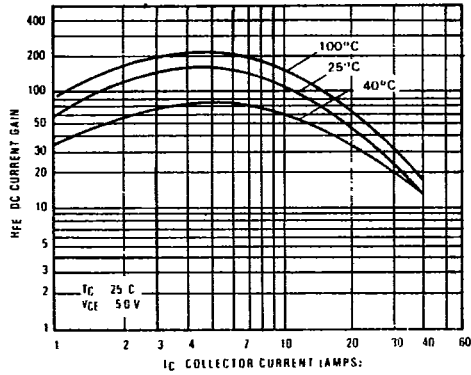


FIGURE 2 — COLLECTOR SATURATION REGION

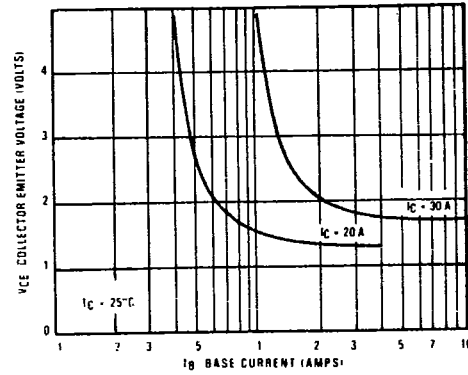


FIGURE 3 — COLLECTOR-EMITTER SATURATION VOLTAGE

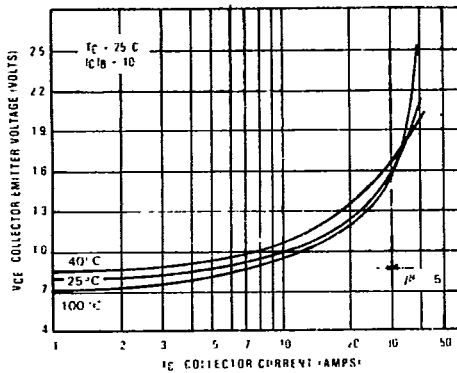


FIGURE 4 — BASE-EMITTER VOLTAGE

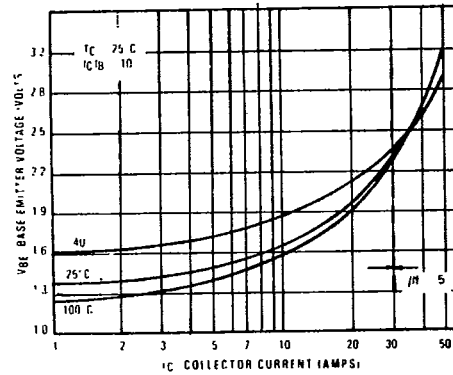


FIGURE 5 — THERMAL RESPONSE

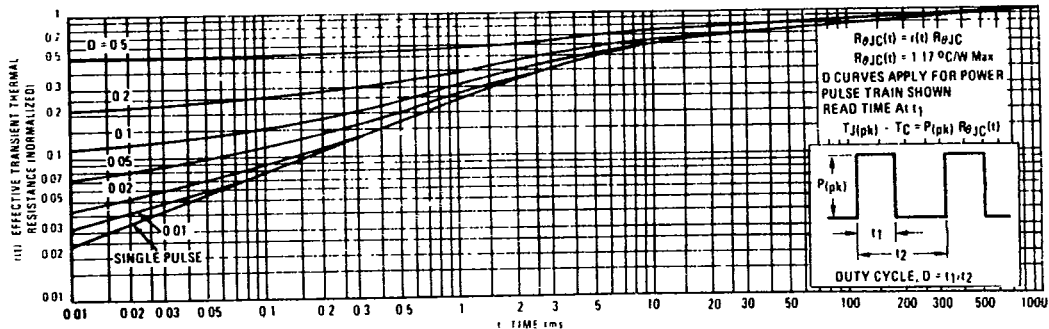


TABLE 1 - TEST CONDITIONS FOR DYNAMIC PERFORMANCE

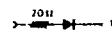
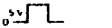
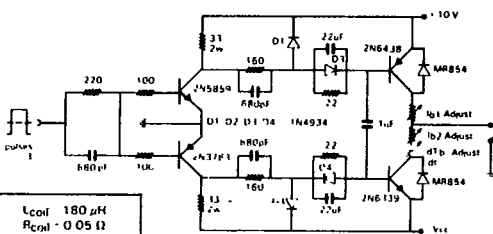
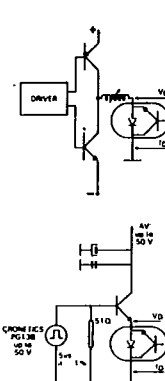
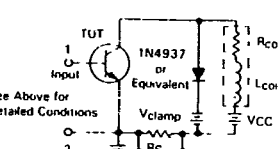
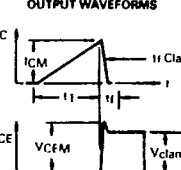
VCE(sus)		RBSOA AND INDUCTIVE SWITCHING		TEST CIRCUIT for FREE WHEEL DIODE
INPUT CONDITIONS	 1  2 PW V and t_r Adjust I_C 100 mA			
CIRCUIT VALUES	L_{coil} 10 mH R_{coil} 0.7 Ω V_{clamp} VCE(sus)	L_{coil} 180 μ H R_{coil} 0.05 Ω V_{CC} 10 V		
TEST CIRCUITS	INDUCTIVE TEST CIRCUIT  See Above for Detailed Conditions OUTPUT WAVEFORMS  t_1 Adjusted to Obtain I_C $t_1 = L_{coil}(I_{CM})$ V_{CC} $t_2 = L_{coil}(I_{CM})$ V_{Lamp} Test Equipment Scope Tektronix 475 or Equivalent			

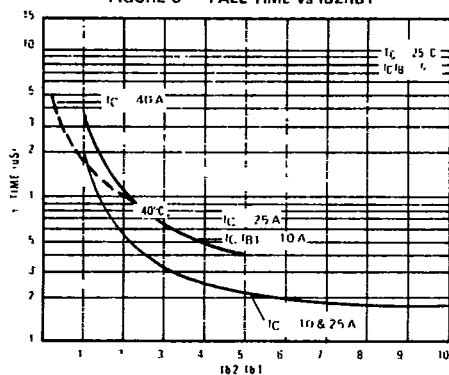
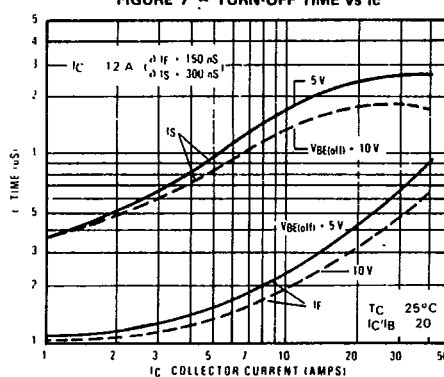
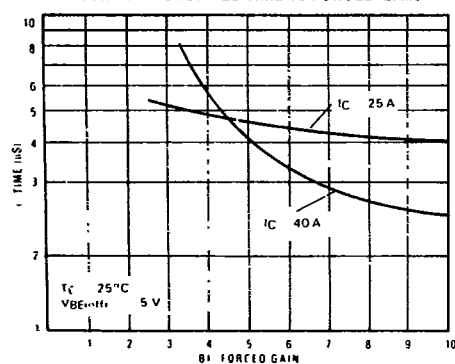
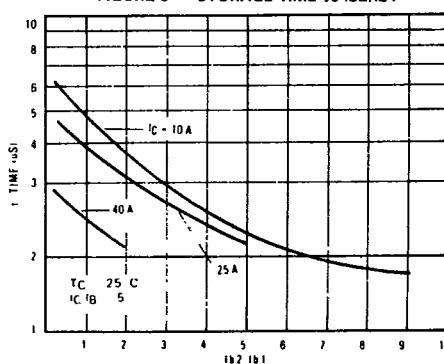
FIGURE 6 FALL TIME vs I_{B2}/I_{B1} FIGURE 7 TURN-OFF TIME vs I_C 

FIGURE 8 STORAGE TIME vs FORCED GAIN

FIGURE 9 STORAGE TIME vs I_{B2}/I_{B1} 

FREE-WHEEL DIODE CHARACTERISTICS

FIGURE 10 — FREE WHEEL DIODE MEASUREMENTS

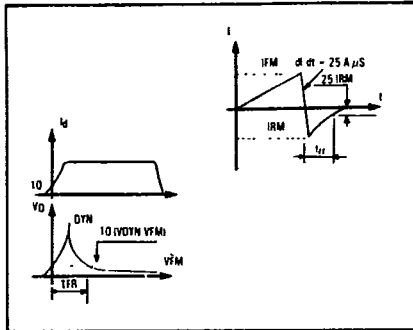


FIGURE 11 — FORWARD VOLTAGE

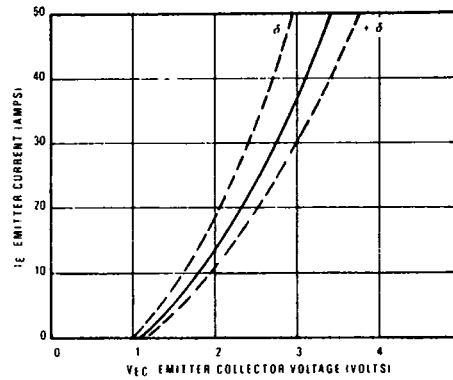


FIGURE 12 — FORWARD MODULATION VOLTAGE

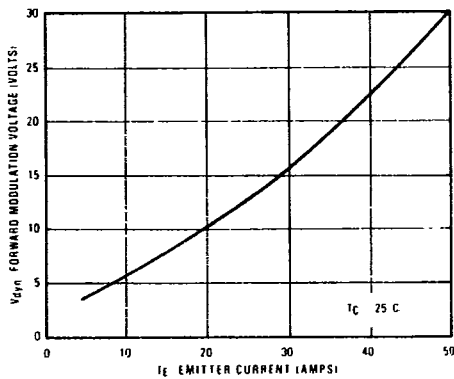


FIGURE 13 — PEAK REVERSE RECOVERY CURRENT

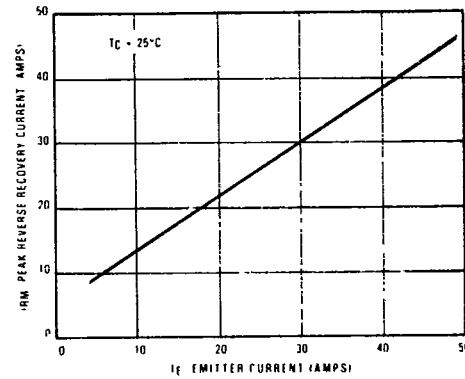


FIGURE 14 — FORWARD RECOVERY TIME

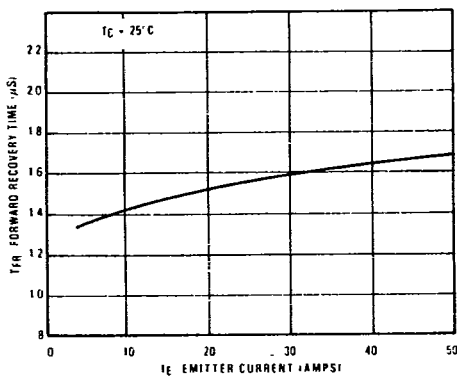
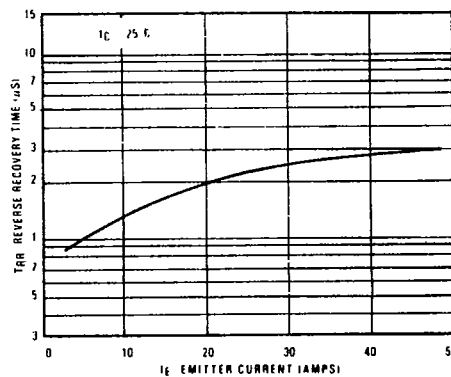


FIGURE 15 — REVERSE RECOVERY TIME



The Safe Operating Area figures shown in Figures 16 and 17 are specified for these devices under the test conditions shown.

FIGURE 16 — SAFE OPERATING AREA

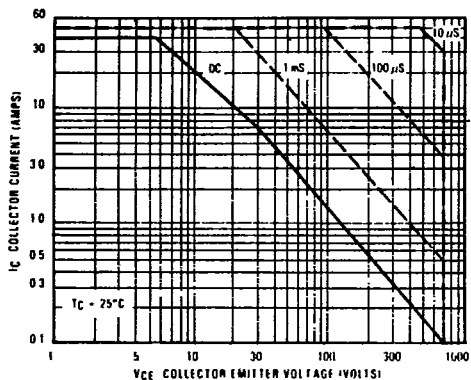


FIGURE 17 — REVERSE BIAS SAFE OPERATING AREA

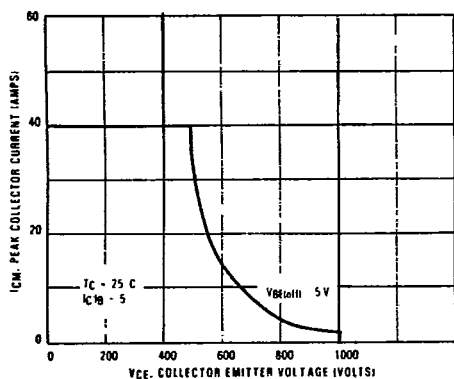
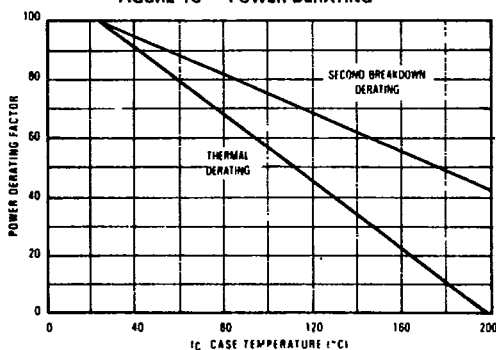


FIGURE 18 — POWER DERATING



SAFE OPERATING AREA INFORMATION

FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subject to greater dissipation than the curves indicate.

The data of Figure 16 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 16 may be found at any case temperature by using the appropriate curve on Figure 18.

$T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

REVERSE BIAS

For inductive loads, high voltage and high current must be sustained simultaneously during turn-off, in most cases, with the base to emitter junction reverse biased. Under these conditions the collector voltage must be held to a safe level at or below a specific value of collector current. This can be accomplished by several means such as active clamping, RC snubbing, load line shaping, etc. The safe level for these devices is specified as Reverse Bias Safe Operating Area and represents the voltage-current condition allowable during reverse biased turn-off. This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode. Figure 17 gives the RBSOA characteristics.